- 5. The method of claim 4, further comprising the step of dispensing a slurry comprising hydrogen peroxide on the polishing pad.
- 5 6. The method of claim 1, wherein the layer of material is further characterized as a tungsten layer.
 - 7. The method of claim 6, further comprising the step of dispensing a slurry comprising ferric nitrate on the polishing pad.
 - 8. The method of claim 1, wherein the layer of material is further characterized as a silicon oxide layer.
 - 9. The method of claim 8, further comprising the step of dispensing a slurry comprising potassium hydroxide on the polishing pad.
 - 10. The method of claim 1, wherein the tapered region is further characterized as having a constant angle taper.
 - 11. The method of claim 1, wherein the tapered region is further characterized as having a variable angle taper.

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- 17. The method of claim 12, wherein the peripheral region comprises a horizontal region.
- 18. The method of claim 12, wherein the peripheral region comprises a tapered region.
 - 19. The method of claim 12, wherein the peripheral region comprises a substantially vertical sidewall.
- 10 20. The method of claim 12, wherein the peripheral region comprises a grooved region.
 - 21. The method of claim 12, further comprising the step of providing a polishing platen having a tapered region, wherein the peripheral region of the polishing pad conforms to the tapered region of the polishing platen.

- 27. The method of claim 22, wherein the peripheral region comprises a horizontal region.
- 28. The method of claim 22, wherein the peripheral region comprises a tapered region.
 - 30. The method of claim 22, wherein the peripheral region comprises a grooved region.
- 10 31. The method of claim 30, wherein the grooved region is further characterized as being U-shaped.
 - 32. The method of claim 30, wherein the grooved region is further characterized as being V-shaped.